SSDM 2001

DATE

Conference: September 26-28, 2001
Short Course: September 25, 2001(in Japanese)

LOCATION

DAIAMOND HOTEL
25 Ichiban-cho, Chiyoda-ku, Tokyo 102-0082 Japan
TEL:+81-3263-2211 FAX:+81-3263-2222
Web site: http://www.diamond-hotel.co.jp/ (in Japanese)

REGISTRATION

The registration desk will be open from Tuesday to Friday. The registration hours are as follows.

September 25	11:00-16:00	(ｼｮｰﾄｺｰｽ)	1FLobby
25	18:00-20:00	(Conference)	2FLobby
26	8:00-18:00		"
27	8:30-18:00		"
28	8:30-15:00		"

Pre-registration is recommended due to the expected large number of participants. In order to pre-register for SSDM 2001, the enclosed Registration Form should be returned with your payment by August 31 to the SSDM 2001 Secretariat. Payment should be made in Japanese yen by bank transfer or bank draft payable to the SSDM 2001 Secretariat. **Credit cards are acceptable from every attendee**: Diners, Master Card, VISA and AMEX. No personal checks will be accepted. After your remittance has been received, the receipt and a voucher for the participant's kit will be sent by the secretariat early in September. Students' contribution is encouraged. We are pleased to discount the student registration fee (5,000 yen).

Bank transfer to SSDM A/C No. 075- 2374600
Daiichi Kangyo Bank, Hongo Branch, Tokyo
第一勧業銀行　本郷支店(店番号(075)　(普) 2374600
口座名：SSDM

	Registration Fee		Short Courses in Japanese	Banquet
	By August 31	After September 1		
Regular	¥35,000	¥40,000	¥10,000	¥6,000
Student	¥5,000		¥1,000	¥3,000
Accompanying Person				¥3,000

1)The conference registration fee covers the conference attendance and includes a copy of the Extended Abstracts.
2)Student fee of Short Course has been changed discounted from ¥5,000 to ¥1,000.
3)Most lecture of the short course are given Japanese (No Translation), while their texts are prepared in English.

REGISTRATION CANCELLATION

Conference:
Cancellation fee of ¥3,000 will be deducted from the refund. Cancellation should be made in writing to the SSDM 2001 Secretariat. No cancellation will be allowed after September 10, 2001. Extended Abstracts will be sent to absent registrants after the Conference.

Short Course:
Regular:¥2,000 will be deducted.,
Student: No fee will be refund.
Cancellations should be made in writing to the SSDM 2001 Secretariat. No cancellation will be allowed after September 10. A text will be sent to absent registrants after the Conference.

BANQUET

A buffet dinner will be held at "Diamond Hall" of the conference site (1F) on September 26 from 18:00-20:00. Tickets (Regular ¥6,000 / Student ¥3,000) can be purchased at the registration desk.

LATE NEWS PAPERS

Late News Paper Deadline is July 31, 2001.

Late news papers describing important new developments may be submitted. A two-page description must be sent in the camera-ready format as required for the regular papers. The accepted papers will be included in the Extended Abstracts.

Original 2-page manuscript, 5 copies of printed or photocopied on both sides of a sheet with attached author's application form and copyright form should be sent to SSDM 2001 Secretariat.

Notice of acceptance will be mailed by the middle of August.

EXTENDED ABSTRACTS AND PUBLICATION

Authors of papers accepted for SSDM 2001 are encouraged to submit the original and significant part of the papers to the Special Issue of the Japanese Journal of Applied Physics. The special issue will be published in April, 2002.

AGREEMENT NOT TO PRE-PUBLISH ABSTRACTS

Submission of an abstract for review and subsequent acceptance is considered by the committee as an agreement that the work will not be published by the author prior to the presentation at the conference. This policy will be enforced by automatic withdrawal of the paper by the conference committee.

AWARDS

"SSDM Awards" will be given to excellent papers presented in the previous conferences.

SSDM Award
for the paper outstandingly contributed to the field of solid state devices and materials, among the papers presented prior to 1995.

SSDM Paper Award
for the best paper presented at the last conference.

SSDM Young Researcher Award
for a few excellent papers by young researchers presented at the last conference.

FINANCIAL SUPPORT

Limited financial support for presentations by students and by researchers from newly industrializing countries are available. People who are interested in the support should directly contact to the Steering Committee, *c/o Business Center for Academic Societies Japan, e-mail: ssdm@bcasj.or.jp.*

VISA REQUIREMENT

All foreign participants must have valid passport. Participants from countries where a visa is required to enter Japan are recommended to apply at the nearest Japanese embassy in their countries as soon as possible.

HOTEL ACCOMMODATIONS

	Room Rates		
Diamond Hotel	Single with bath	Twin with bath	25 Ichiban-cho, Chiyoda-ku, Tokyo 102-0082 Japan Phone: +81-3-3263-2211 Fax: +81-3-3263-2222 E-mail:FJP00503@nifty.com
	¥9,240	¥16,940	

Notes:
*Room rates include service charge. But a 5% tax will be added to your bill.
*Room rates include no meals.
*The hotel reservations run the first-come, first-serve basis; therefore, the bookings will close as soon as all the rooms are reserved.

APPLICATION AND PAYMENT FOR HOTELS

Participants wishing to reserve hotel accommodations should complete the application form and return it by fax or by mail to reach Diamond Hotel **no later than August 25, 2001**. All payment must be in Japanese yen.
Payment should be in the form of:
-- The following credit cards are acceptable:
1. Visa Card 2. MasterCard 3. Diners Club 4. AMEX
Please bear in mind that you will be required to present the credit card once again upon check-in.

INSURANCE

The organizer cannot accept responsibility for accidents that might occur. Delegates are encouraged to obtain travel insurance (medical, personal accident, and luggage) in their home country prior to departure.

CLIMATE

The temperature in Tokyo during the period of the Conference ranges between 18℃ and 24℃.

ELECTRICAL APPLIANCES

Japan operates on 100 volts for electrical appliances. The frequency is 50 Hz in eastern Japan including Tokyo and 60 Hz in western Japan including Kyoto and Osaka.

RUMP SESSIONS

September 27 (Thursday) 18:30-20:30
Rump session A (Room A)
Organizer: T. Kikkawa (Hiroshima Univ.)
Title : Next Generation ULSI: Challenge and Breakthrough The challenge and breakthrough technologies for the next generation ULSIs will be discussed from various aspects such as transistors, circuts, RF clock distribution, lithography, ferroelectric materials and

nonvolatile memories.

Rump session B (Diamond Hall)
Title:

SHORT COURSES

Two Short courses will be held on September 25 (Tuesday) for young engineers and students. All lectures are given in Japanese.

Secretariat of SSDM
c/o Business Center for Academic Societies Japan
5-16-9 Honkomagome, Bunkyo-ku, Tokyo 113-8622, Japan
Phone: ＋81-3-5814-5800 FAX: ＋81-3-5814-5823
E-mail: ssdm@bcasj.or.jp

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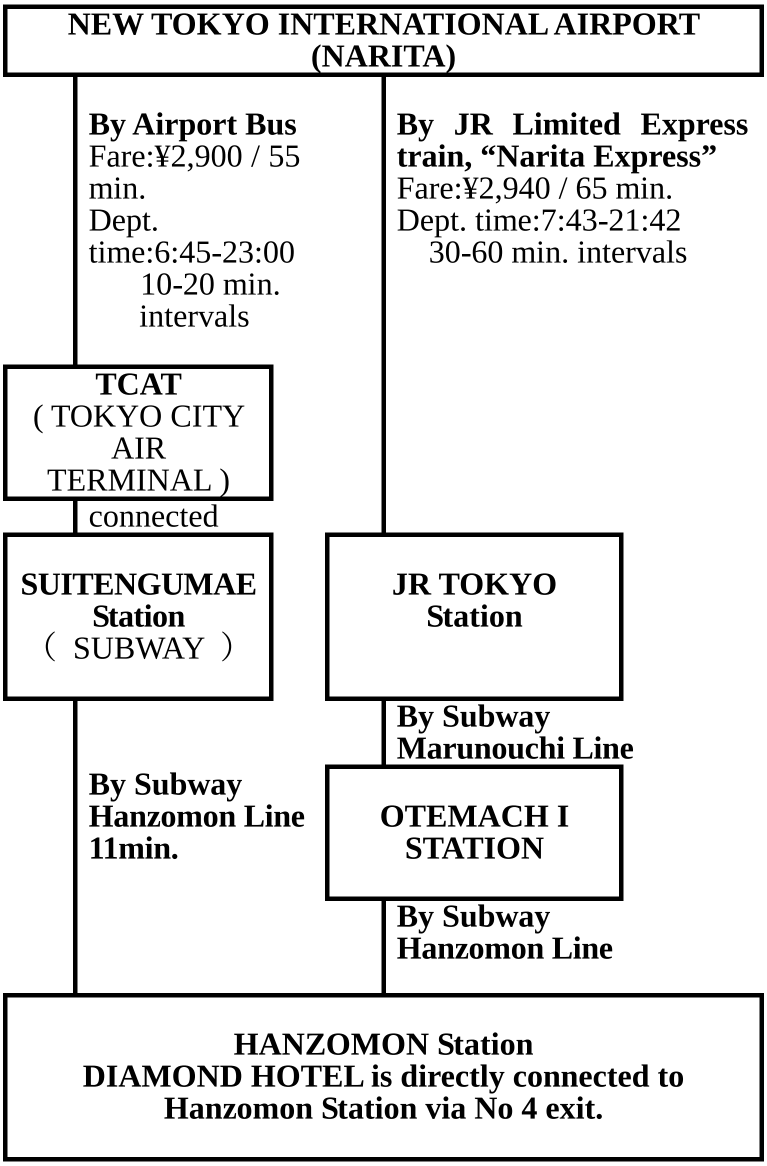

NEW TOKYO INTERNATIONAL AIRPORT (NARITA)

By Airport Bus
Fare:¥2,900 / 55 min.
Dept. time:6:45-23:00
10-20 min. intervals

By JR Limited Express train, “Narita Express”
Fare:¥2,940 / 65 min.
Dept. time:7:43-21:42
30-60 min. intervals

TCAT
(TOKYO CITY AIR TERMINAL)

connected

SUITENGUMAE Station
（ SUBWAY ）

JR TOKYO Station

By Subway Marunouchi Line

OTEMACH I STATION

By Subway Hanzomon Line 11min.

By Subway Hanzomon Line

HANZOMON Station
DIAMOND HOTEL is directly connected to Hanzomon Station via No 4 exit.